

SavantIC Semiconductor

Product Specification

Silicon PNP Darlington Power Transistors

TIP125/126/127

DESCRIPTION

- With TO-220C package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage
- Complement to type TIP120/121/122

APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

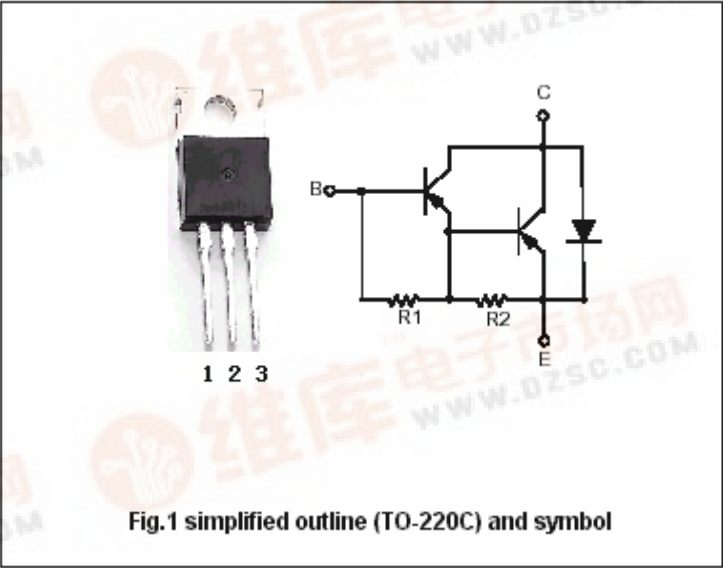


Fig.1 simplified outline (TO-220C) and symbol

ABSOLUTE MAXIMUM RATINGS(T_c=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	TIP125	Open emitter	-60	V
		TIP126		-80	
		TIP127		-100	
V _{CEO}	Collector-emitter voltage	TIP125	Open base	-60	V
		TIP126		-80	
		TIP127		-100	
V _{EBO}	Emitter-base voltage		Open collector	-5	V
I _C	Collector current-DC			-5	A
I _{CM}	Collector current-Pulse			-8	A
I _B	Base current-DC			-120	mA
P _C	Collector power dissipation	T _c =25℃		65	W
		T _a =25℃		2	
T _j	Junction temperature			150	℃
T _{stg}	Storage temperature			-65~150	℃



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CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	TIP125	I _C =-0.1A, I _B =0	-60			V
		TIP126		-80			
		TIP127		-100			
V _{CE(sat)-1}	Collector-emitter saturation voltage		I _C =-3A, I _B =-12mA			-2.0	V
V _{CE(sat)-2}	Collector-emitter saturation voltage		I _C =-5A, I _B =-20mA			-4.0	V
V _{BE}	Base-emitter on voltage		I _C =-3.0A; V _{CE} =-3V			-2.5	V
I _{CBO}	Collector cut-off current	TIP125	V _{CB} =-60V, I _E =0			-0.2	mA
		TIP126	V _{CB} =-80V, I _E =0				
		TIP127	V _{CB} =-100V, I _E =0				
I _{CEO}	Collector cut-off current	TIP125	V _{CE} =-30V, I _B =0			-0.5	mA
		TIP126	V _{CE} =-40V, I _B =0				
		TIP127	V _{CE} =-50V, I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-2	mA
h _{FE-1}	DC current gain		I _C =-0.5A; V _{CE} =-3V	1000			
h _{FE-2}	DC current gain		I _C =-3.0A; V _{CE} =-3V	1000			
C _{OB}	Output capacitance		I _E =0; V _{CB} =-10V, f=0.1MHz			300	pF

TIP125/126/127

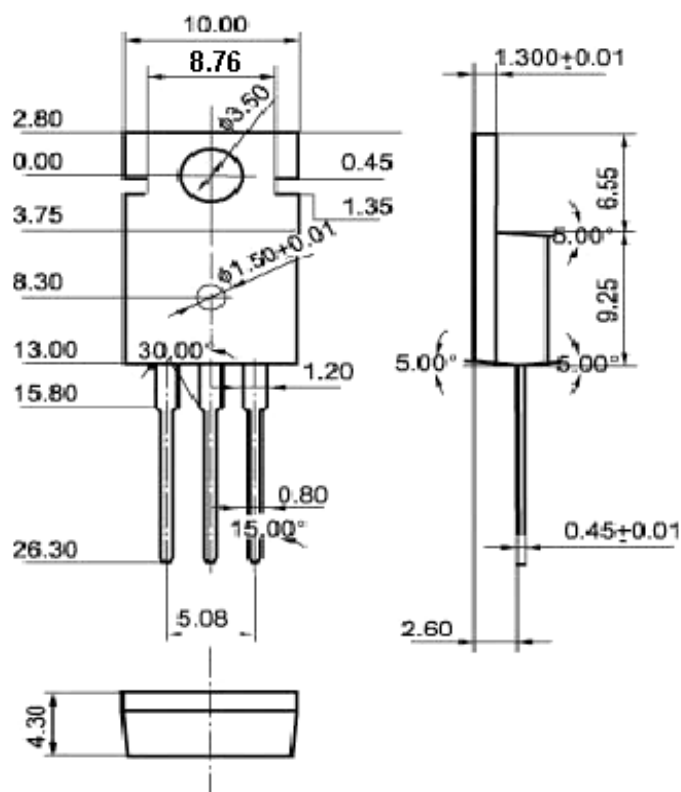


Fig.2 Outline dimensions

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